SKM 100GB123D

SEMITRANS® 2

IGBT Modules

SKM 100GB123D

SKM 100GAL123D

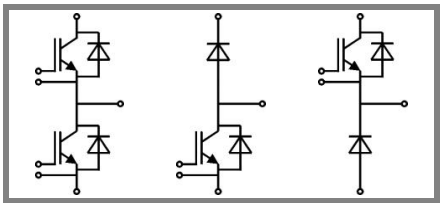
SKM 100GAR123D

Features

- MOS input (voltage controlled)
- N channel, Homogeneous Si
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to 6 x I_{cnom}
- Latch-up free
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DCB Direct Copper Bonding Technology
- Large clearance (10 mm) and creepage distances (20 mm)

Typical Applications

- AC inverter drives
- UPS



GB GAL GAR

Absolute Maximum Ratings			T_c = 25 °C, unless otherwise specified	
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	T_j = 150 °C	T_{case} = 25 °C	100	A
		T_{case} = 80 °C	90	A
I_{CRM}	I_{CRM}=2xI_{Cnom}, t_p = 1 ms		150	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 600 V; $V_{GE} \leq$ 20 V; V_{CES} < 1200 V	T_j = 125 °C	10	µs
Inverse Diode				
I_F	T_j = 150 °C	T_{case} = 25 °C	95	A
		T_{case} = 80 °C	65	A
I_{FRM}	I_{FRM} = 2xI_{Fnom}, t_p = 1 ms		150	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 150 °C	720	A
Freewheeling Diode				
I_F	T_j = 150 °C	T_{case} = 25 °C	130	A
		T_{case} = 80 °C	90	A
I_{FRM}	I_{FRM} = 2xI_{Fnom}, t_p = 1 ms		200	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 150 °C	900	A
Module				
$I_{t(RMS)}$			200	A
T_{vj}			- 40... + 150	°C
T_{stg}	$T_{OPERATION} \leq T_{stg}$		- 40...+ 125	°C
V_{isol}	AC, 1 min.		2500	V

Characteristics			T_c = 25 °C, unless otherwise specified			
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 2 mA		4,5	5,5	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C		0,1	0,3	mA
V_{CE0}		T_j = 25 °C		1,4	1,6	V
		T_j = 125 °C		1,6	1,8	V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		14,6	18,6	mΩ
		T_j = 125°C		20	25,3	mΩ
$V_{CE(sat)}$	I_{Cnom} = 75 A, V_{GE} = 15 V	T_j = °$C_{chiplev.}$		2,5	3	V
C_{ies}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		5	6,6	nF
C_{oes}				0,72	0,9	nF
C_{res}				0,38	0,5	nF
Q_G	V_{GE} = -8V - +20V			750		nC
R_{Gint}	T_j = °C			5		Ω
$t_{d(on)}$	R_{Gon} = 15 Ω	V_{CC} = 600V		30	60	ns
t_r		I_{Cnom}= 75A		70	140	ns
E_{on}		T_j = 125 °C		10		mJ
$t_{d(off)}$	R_{Goff} = 15 Ω	V_{GE} = ± 15V		450	600	ns
t_f				70	90	ns
E_{off}				8		mJ
$R_{th(j-c)}$	per IGBT				0,18	K/W

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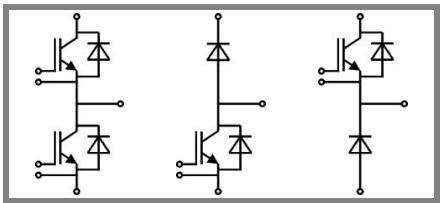

GB GAL GAR

Characteristics

Symbol	Conditions		min.	typ.	max.	Units
Inverse Diode						
$V_F = V_{EC}$	I_{Fnom} = 75 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		2	2,5	V
		T_j = 125 °$C_{chiplev.}$		1,8		V
V_{F0}		T_j = 25 °C		1,1	1,2	V
		T_j = 125 °C				V
r_F		T_j = 25 °C		12	17	mΩ
		T_j = 125 °C				mΩ
I_{RRM}	I_{Fnom} = 75 A	T_j = 125 °C		40		A
Q_{rr}	di/dt = 800 A/µs			3		µC
E_{off}	V_{GE} = 0 V; V_{CC} = 600 V					mJ
$R_{th(j-c)D}$	per diode				0,5	K/W
Freewheeling Diode						
$V_F = V_{EC}$	I_{Fnom} = 100 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		2	2,5	V
		T_j = 125 °$C_{chiplev.}$		1,8		V
V_{F0}		T_j = 25 °C		1,1	1,2	V
		T_j = 125 °C				V
r_F		T_j = 25 °C		9	13	V
		T_j = 125 °C				V
I_{RRM}	I_{Fnom} = 100 A	T_j = 25 °C		50		A
Q_{rr}	di/dt = 1000 A/µs			5		µC
E_{off}	V_{GE} = 0 V; V_{CC} = 600 V					mJ
$R_{th(j-c)FD}$	per diode				0,36	K/W
Module						
L_{CE}					30	nH
$R_{CC'+EE'}$	res., terminal-chip	T_{case}= 25 °C		0,75		mΩ
		T_{case}= 125 °C		1		mΩ
$R_{th(c-s)}$	per module				0,05	K/W
M_s	to heat sink M6		3		5	Nm
M_t	to terminals M5		2,5		5	Nm
w					160	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

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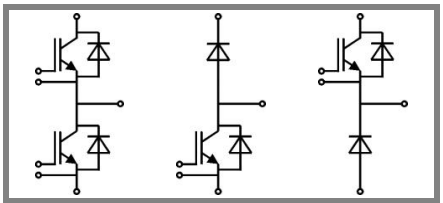


GB GAL GAR

Z_{th} Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	i = 1	162	mk/W
R_i	i = 2	14	mk/W
R_i	i = 3	2,7	mk/W
R_i	i = 4	1,3	mk/W
tau_i	i = 1	0,204	s
tau_i	i = 2	0,0242	s
tau_i	i = 3	0,0013	s
tau_i	i = 4	0	s
$Z_{th(j-c)D}$			
R_i	i = 1	320	mk/W
R_i	i = 2	150	mk/W
R_i	i = 3	0,0265	mk/W
R_i	i = 4	3,5	mk/W
tau_i	i = 1	0,05	s
tau_i	i = 2	0,0104	s
tau_i	i = 3	0,0034	s
tau_i	i = 4	0,0003	s

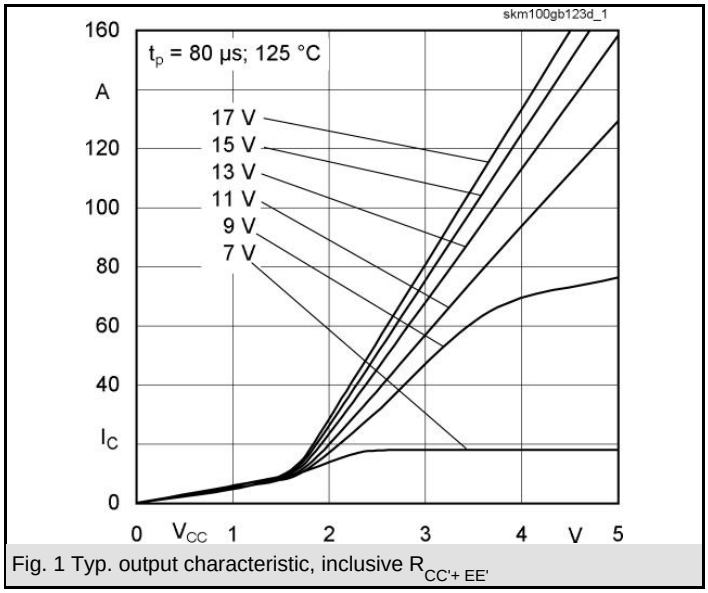


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

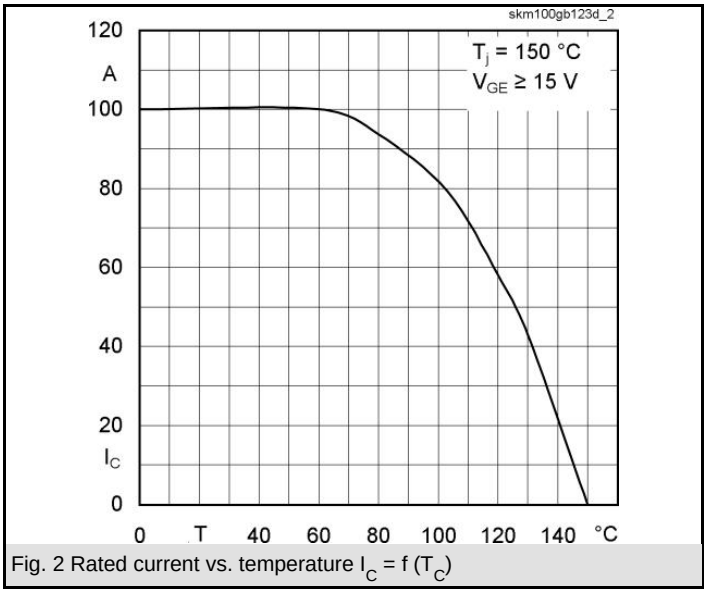


Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

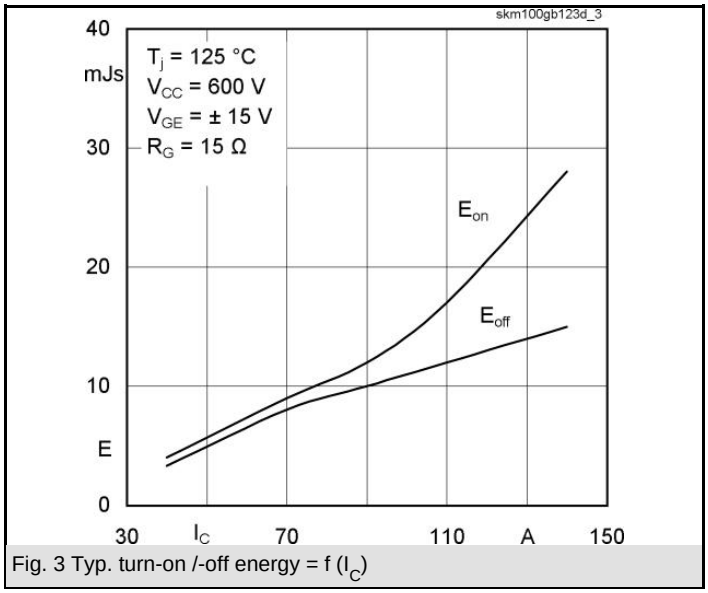


Fig. 3 Typ. turn-on /-off energy = f (I_C)

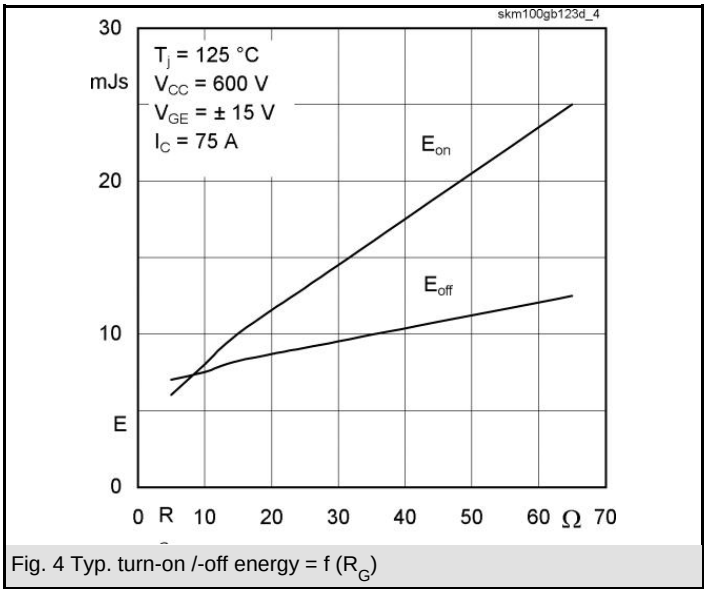


Fig. 4 Typ. turn-on /-off energy = f (R_G)

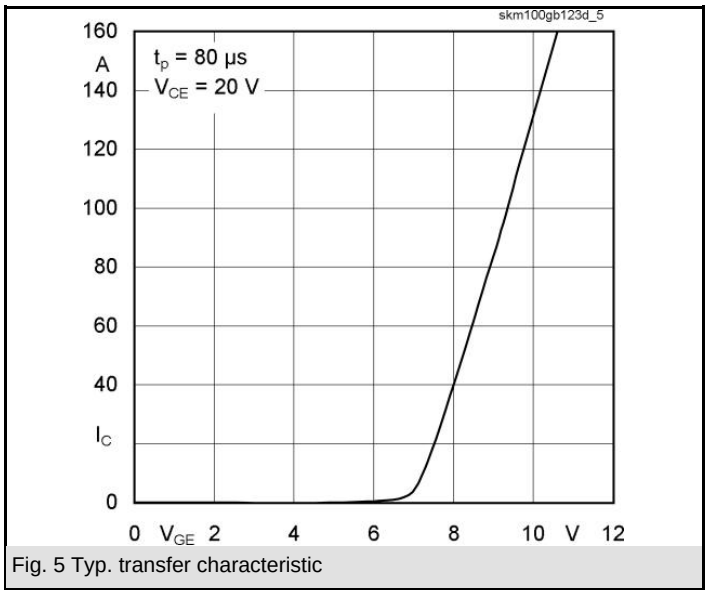


Fig. 5 Typ. transfer characteristic

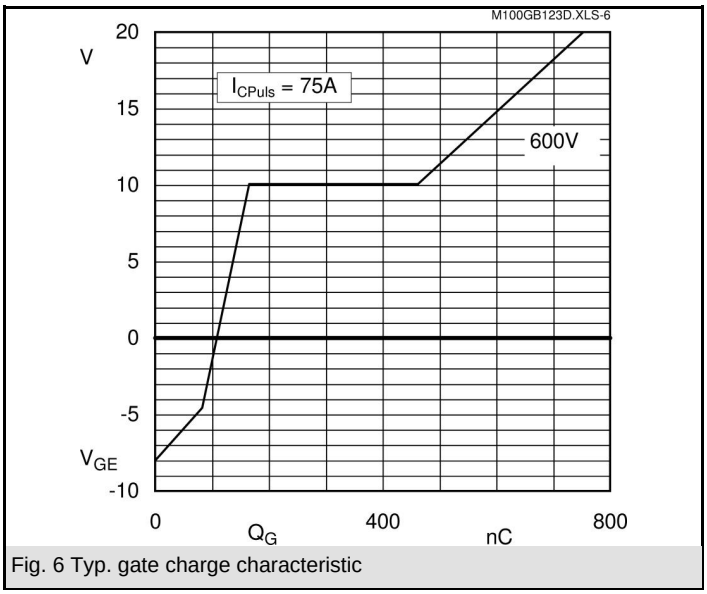


Fig. 6 Typ. gate charge characteristic

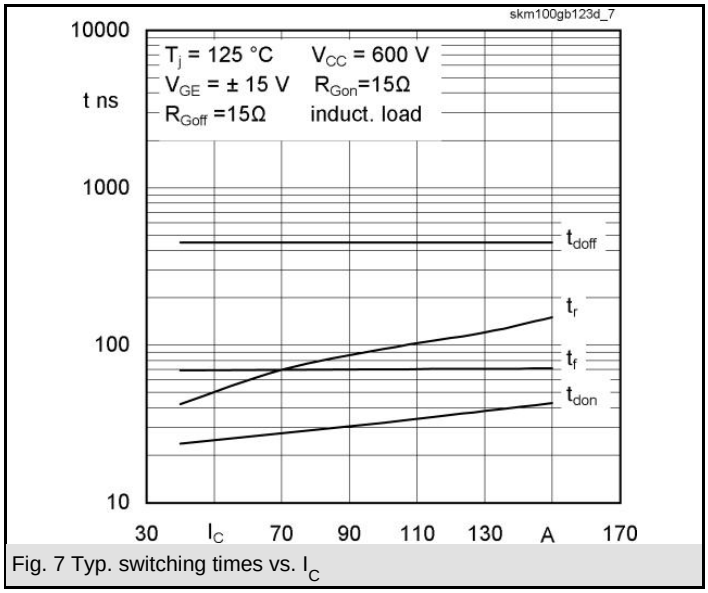


Fig. 7 Typ. switching times vs. I_C

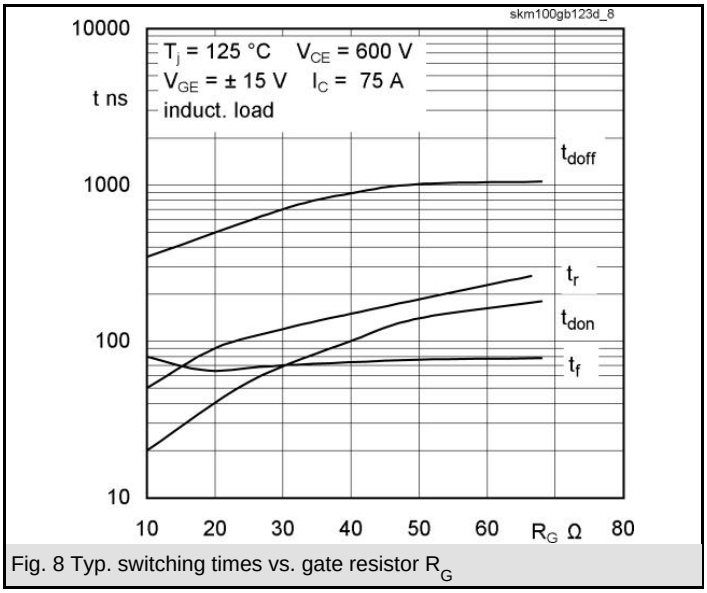


Fig. 8 Typ. switching times vs. gate resistor R_G

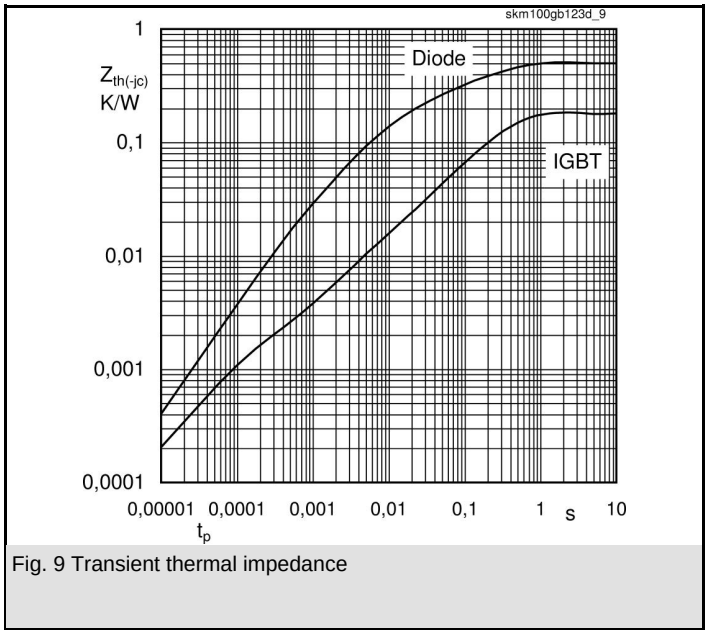


Fig. 9 Transient thermal impedance

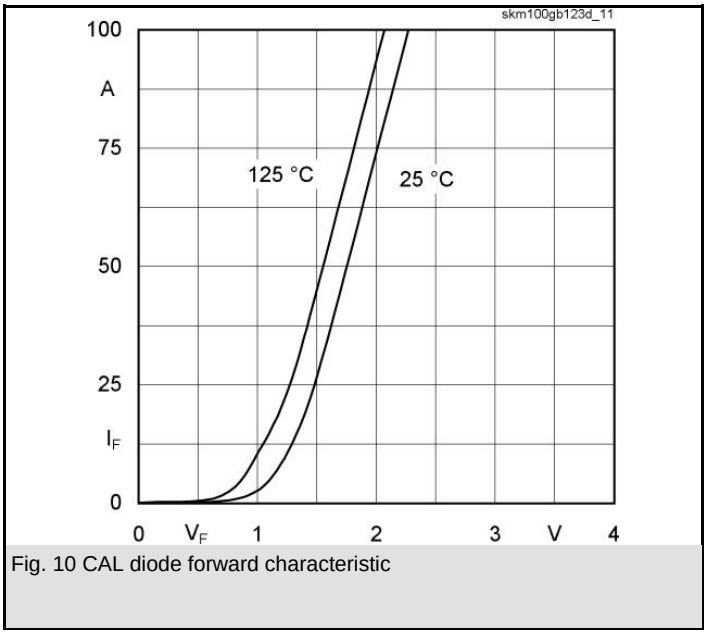


Fig. 10 CAL diode forward characteristic

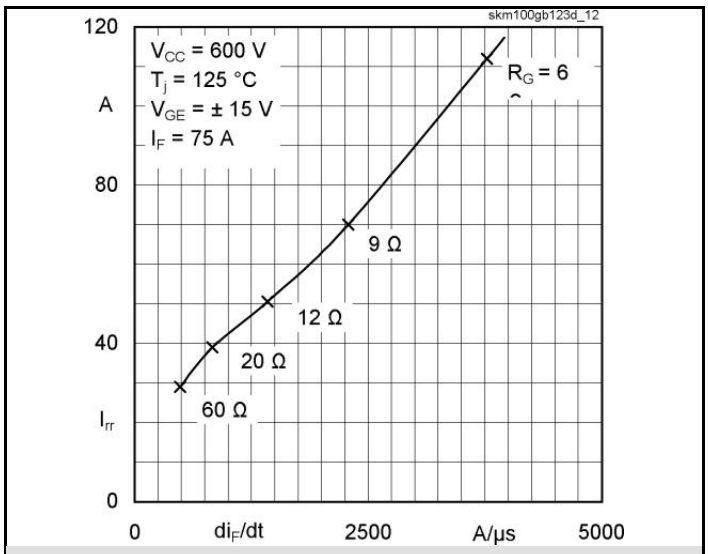


Fig. 11 Typ. CAL diode peak reverse recovery current

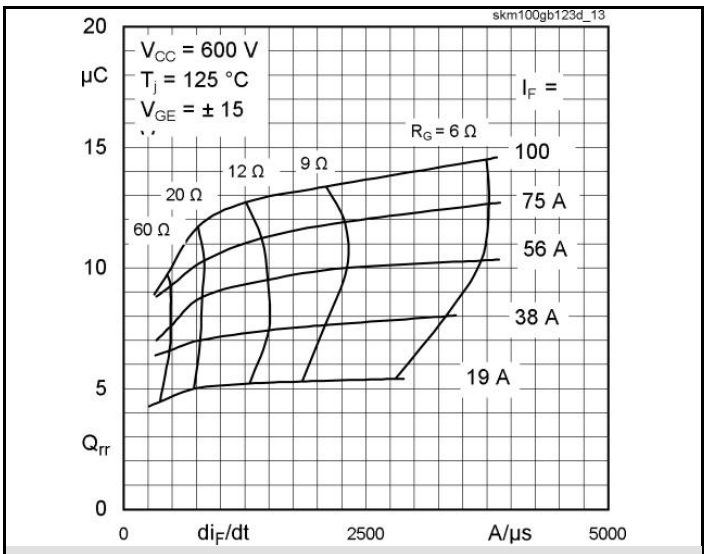
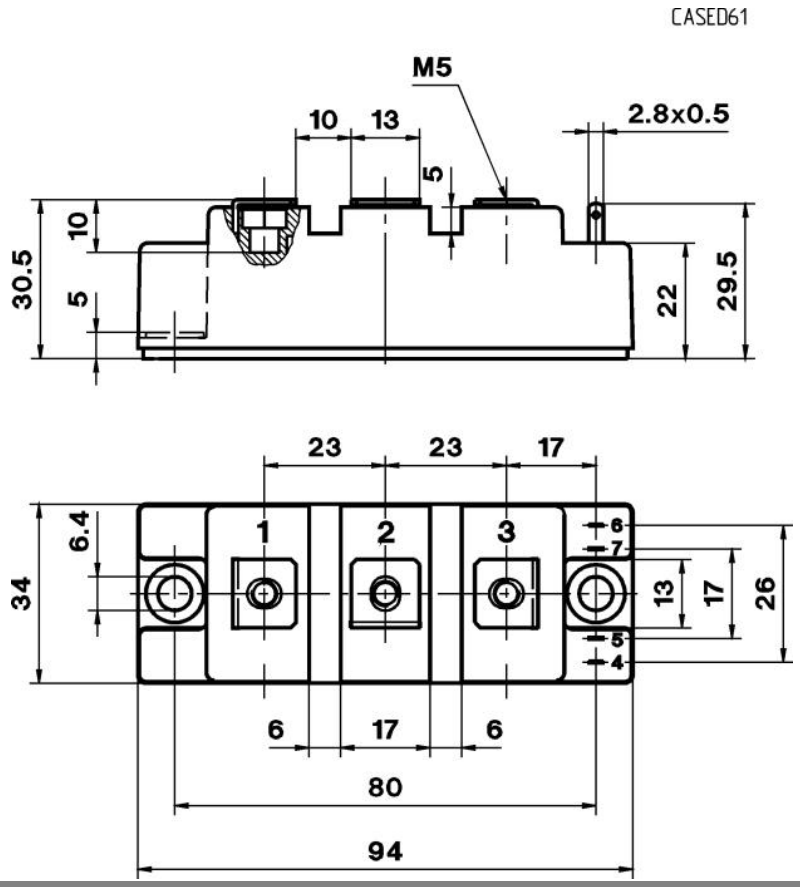


Fig. 12 Typ. CAL diode peak reverse recovery charge

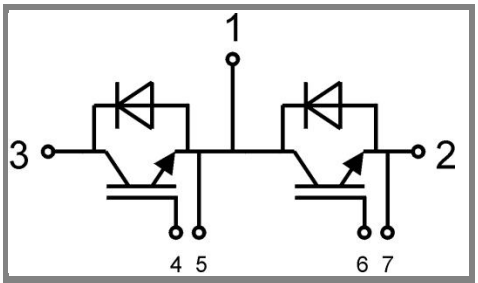
SKM 100GB123D

UL Recognized
File no. E 63 532

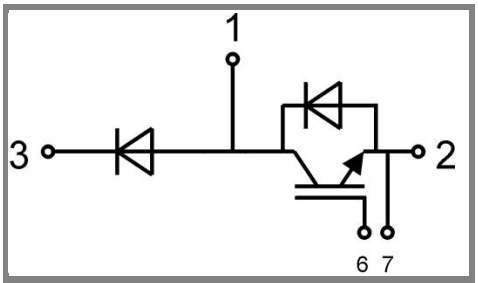
Dimensions in mm



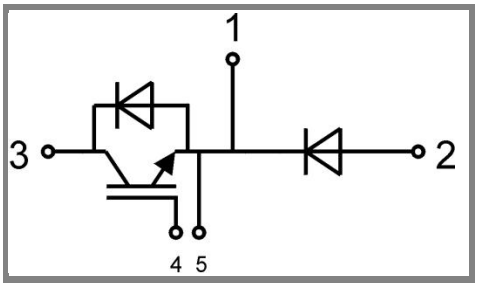
Case D 61



GB Case D 61



GAL Case D 62 (➞ D 61)



GAR Case D 63 (➞ D 61)

